

GATE STRUCTURES IN NONVOLATILE MEMORY DEVICES HAVING
CURVED SIDE WALLS FORMED USING OXYGEN PATHWAYS AND
METHODS OF FORMING SAME

5

ABSTRACT

Gate structures of a non-volatile integrated circuit memory device can include
a thermal oxidation layer on a substrate beneath the gate structure that defines a side
wall of the gate structure. An oxygen diffusion barrier layer is on the side wall of the
gate structure and a floating gate is on the thermal oxidation layer and has a curved
10 side wall portion. Related methods are also discussed.